



SOT-23 Plastic-Encapsulate Transistors

S8550D TRANSISTOR (PNP)

FEATURES

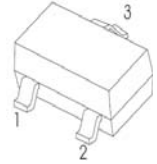
- High Collector Current
- Complementary TO S8050D
- Excellent h_{FE} Linearity

MARKING: 2TY

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-800	mA
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	416	$^\circ\text{C}/\text{W}$
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

SOT - 23



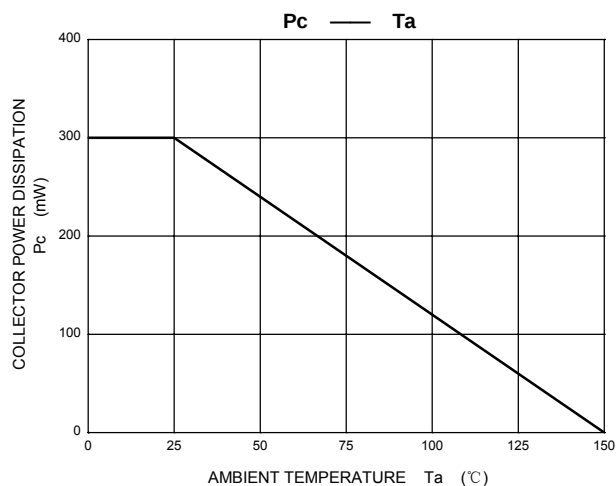
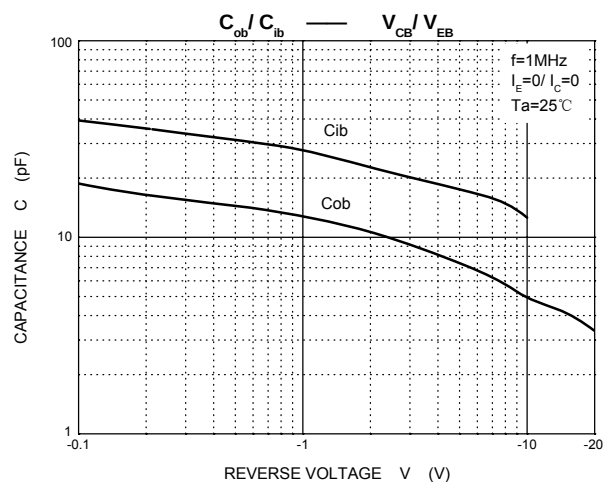
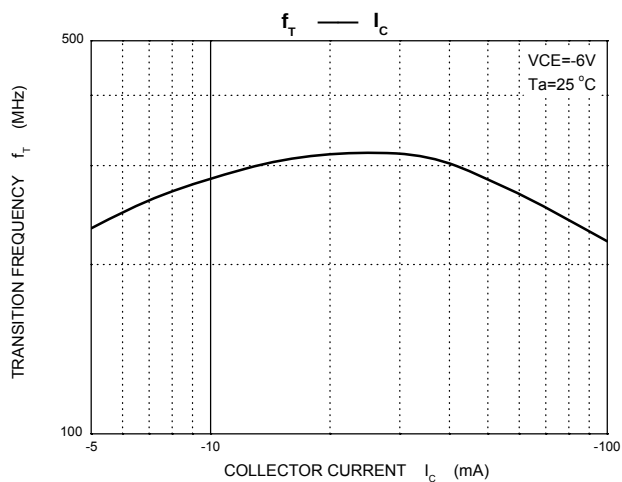
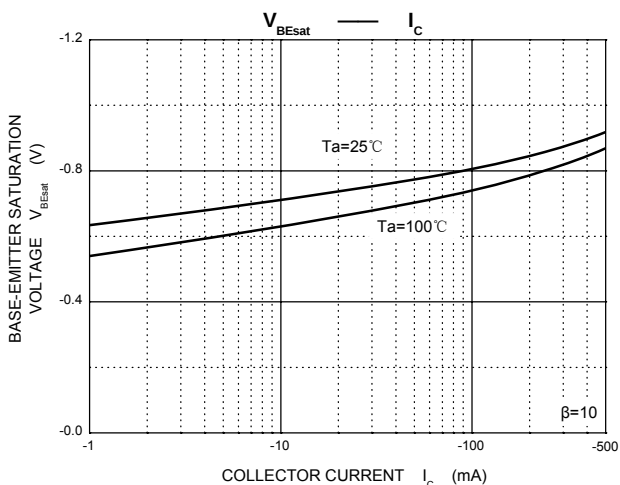
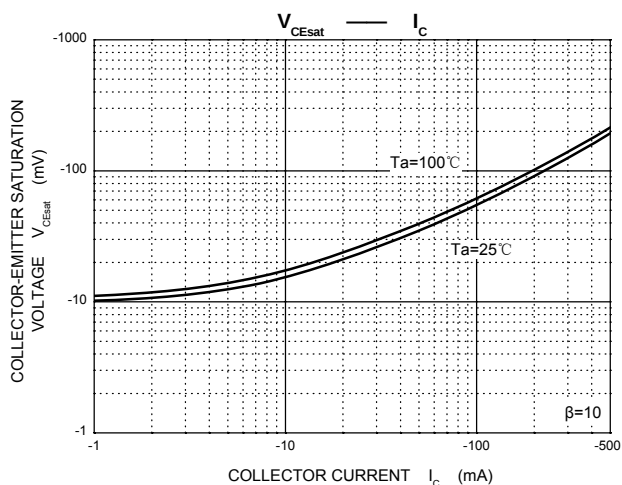
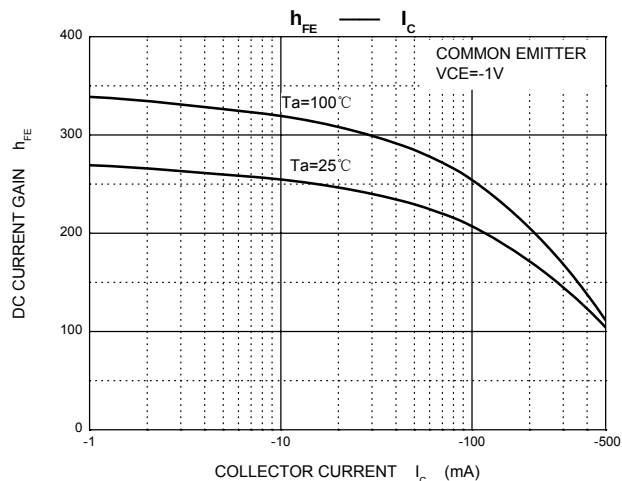
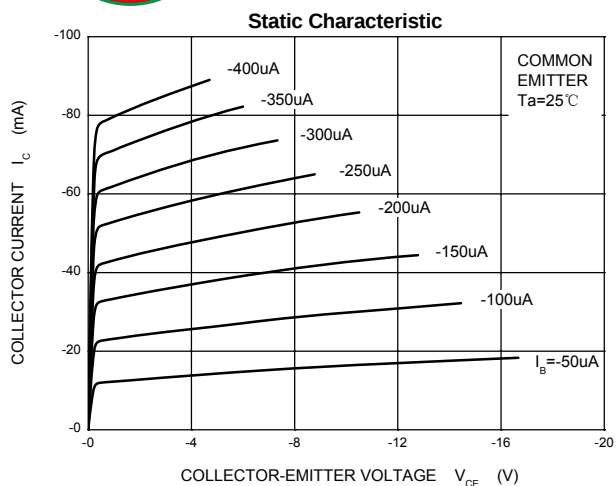
1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1\text{mA}$, $I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1\text{mA}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}$, $I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20\text{V}$, $I_B=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}$, $I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1\text{V}$, $I_C=-50\text{mA}$	200		350	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE}=-6\text{V}$, $I_C=-20\text{mA}$, $f=30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$			5	pF



2TY



MARKING:

1.BASE

2. EMITTER

3.COLLECTOR

